

IN THE UNITED STATES PATENT  
AND TRADEMARK OFFICE

2822  
#9/Amendment  
Ford  
1/26/03

Applicants: Kim et al.

Serial No.: 10/032,687

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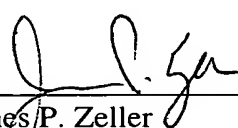
For: METHOD OF FORMING  
WIRING IN SEMICONDUCTOR  
DEVICES

Group Art Unit: 2822

Examiner: Maria F. Guerrero

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January 15, 2003

  
James P. Zeller  
Reg. No. 28,491

AMENDMENT "A"

Commissioner for Patents  
Washington, D.C. 20231

Sir:

Please amend this application as follows:

IN THE SPECIFICATION:

The paragraph beginning at page 5, line 21 has been changed as follows:

Referring to Fig. 4A, a gate oxide film 2, a polysilicon layer 3, a metal layer 4 and a hard mask layer 5 are sequentially formed on a semiconductor substrate 1. Then, photolithographic film patterns 6 are formed on the hard mask layer 5. The metal layer 4 is made of metal such as aluminum (Al), tungsten (W) and titanium (Ti) or silicide. The hard mask layer 5 uses a nitride film deposited by low-pressure chemical vapor deposition (LPCVD) using SiH<sub>4</sub> and NH<sub>3</sub> in a single type chamber capable of processing a wafer one by one. The deposition process includes the following conditions: the temperature is 600°C to 800°C and the pressure is over 1 Torr, preferably, 1 Torr to 500 Torr. Also, the nitride film is formed in a thickness of 500Å to 3000Å.

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